IN THE CLAIMS:

Please AMEND claims 1, 3, 5, 7, 8, and 10, and please CANCEL claims 2, 6, 9, and 11 without prejudice or disclaimer in accordance with the following:

1. (**CURRENTLY AMENDED**) A high density recording medium with a super-resolution near-field structure including a sequential stack of a second dielectric layer, a recording layer, a protective layer, a mask layer, a first dielectric layer, and a polycarbonate layer, wherein the mask layer comprises ~~high-melting-point metal oxide~~ WO_x to generate a near field by optically or thermally inducing physical changes in the crystalline structure and optical properties of the WO_x~~high-melting-point metal oxide~~.

2. (**CANCELED**)

3. (**CURRENTLY AMENDED**) A high density recording medium with a super-resolution near-field structure including a sequential stack of a second dielectric layer, a recording layer, a protective layer, a mask layer, a first dielectric layer, and a polycarbonate layer, wherein the mask layer comprises TaO_x or AuO_x to generate a near field by optically or thermally inducing physical changes in the crystalline structure and optical properties of the TaO_x or AuO_x~~high-density recording medium of claim 1, wherein the high-melting-point metal oxide for the mask layer is TaO_x or AuO_x which shows irreversible physical changes~~.

4. (**CANCELED**)

5. (**CURRENTLY AMENDED**) The high density recording medium of claim 1, further comprising a reflective layer containing silver or aluminum ~~below~~ disposed on an opposite side of the second dielectric layer from the recording layer.

6. (**CANCELED**)

7. (**CURRENTLY AMENDED**) The high density recording medium of claim 3,

further comprising a reflective layer containing silver or aluminum ~~below~~ disposed on an opposite side of the second dielectric layer from the recording layer.

8. (**CURRENTLY AMENDED**) A high density recording medium with a super-resolution near-field structure including a sequential stack of a second dielectric layer, a recording layer, a protective layer, a mask layer, a first dielectric layer, and a polycarbonate layer, wherein the mask layer consists of SiO_x ~~comprises silicon oxide~~ to generate a near field by optically or thermally inducing physical changes in the crystalline structure and optical properties of the silicon oxide.

9. (**CANCELED**)

10. (**CURRENTLY AMENDED**) The high density recording medium of claim 8, further comprising a reflective layer containing silver or aluminum ~~below~~ disposed on an opposite side of the second dielectric layer from the recording layer.

11. (**CANCELED**)